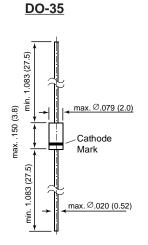
1N914

SMALL SIGNAL DIODE



FEATURES

- Silicon Epitaxial Planar Diode
- For general purpose and switching.



MECHANICAL DATA

Case: DO-35 Glass Case Weight: approx. 0.13 g

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOL	VALUE	UNIT
Peak Reverse Voltage	Vrm	100	V
Maximum Average Rectified Current	lo	75	mA
Maximum Power Dissipation at T _{amb} = 25 °C	Ptot	500	mW
Maximum Junction Temperature	Tj	200	°C
Maximum Forward Voltage Drop at IF = 10 mA	VF	1.0	V
Maximum Reverse Current at $V_R = 20 V$ $V_R = 75 V$	IR	25 5.0	nA μA
Max. Reverse Recovery Time at IF = IR = 10 mA, VR = 6 V, RL = 100 Ω , to Irr = 1 mA	trr	4.0	ns
Maximum Capacitance at V _R =0, f=1.0 MH _Z	Ctot	4.0	pF

